



**Advanced Power
Electronics Corp.**

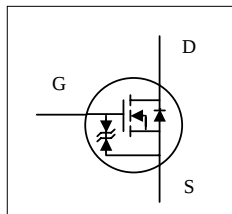
AP9T18GEH/J

Pb Free Plating Product

N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

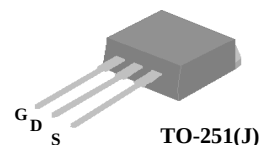
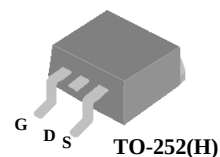
- ▼ G-S Diode embedded
- ▼ Capable of 2.5V gate drive
- ▼ Surface mount package
- ▼ RoHS Compliant



BV_{DS}	20V
$R_{DS(ON)}$	14m Ω
I_D	40A

Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 4.5V	40	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 4.5V	25	A
I_{DM}	Pulsed Drain Current ¹	160	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	31	W
	Linear Derating Factor	0.25	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Thermal Resistance Junction-case Max.	4	$^\circ\text{C}/\text{W}$
Rthj-a	Thermal Resistance Junction-ambient Max.	110	$^\circ\text{C}/\text{W}$

Data and specifications subject to change without notice

200523061-1/4

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	-	-	V
$\Delta BV_{DSS} / \Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =1mA	-	0.02	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V, I _D =20A	-	-	14	mΩ
		V _{GS} =2.5V, I _D =10A	-	-	28	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	0.4	-	1.5	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =20A	-	20	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =20V, V _{GS} =0V	-	-	1	uA
	Drain-Source Leakage Current (T _j =150°C)	V _{DS} =16V, V _{GS} =0V	-	-	25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±12V	-	-	±30	uA
Q _g	Total Gate Charge ²	I _D =20A	-	16	26	nC
Q _{gs}	Gate-Source Charge	V _{DS} =16V	-	2	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	6	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =10V	-	8	-	ns
t _r	Rise Time	I _D =20A	-	84	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =1.0Ω, V _{GS} =5V	-	19	-	ns
t _f	Fall Time	R _D =0.5Ω	-	14	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	1080	1730	pF
C _{oss}	Output Capacitance	V _{DS} =20V	-	205	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	145	-	pF
R _g	Gate Resistance	f=1.0MHz	-	3.6	5.4	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =20A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time ²	I _S =20A, V _{GS} =0V,	-	26	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	19	-	nC

Notes:

- 1.Pulse width limited by safe operating area.
- 2.Pulse width ≤300us , duty cycle ≤2%.

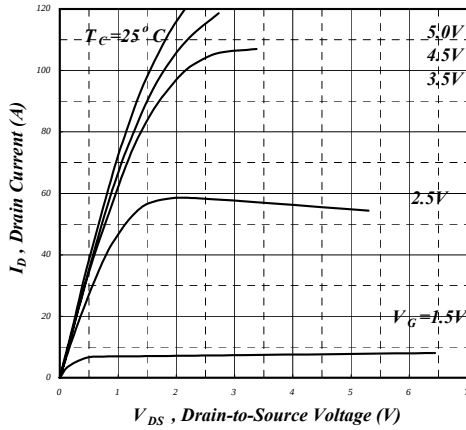


Fig 1. Typical Output Characteristics

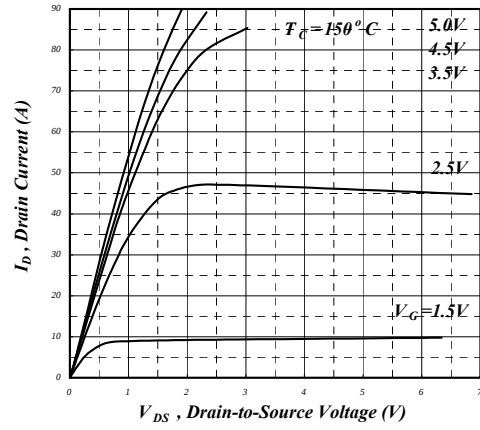


Fig 2. Typical Output Characteristics

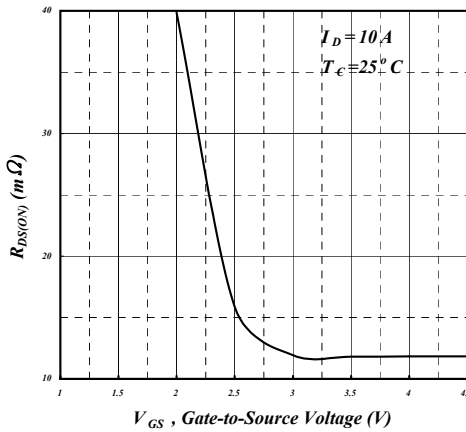


Fig 3. On-Resistance v.s. Gate Voltage

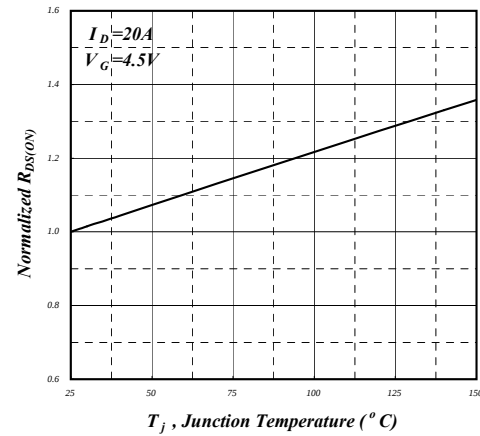


Fig 4. Normalized On-Resistance v.s. Junction Temperature

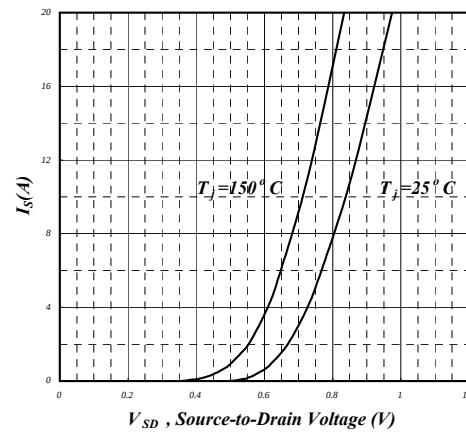


Fig 5. Forward Characteristic of Reverse Diode

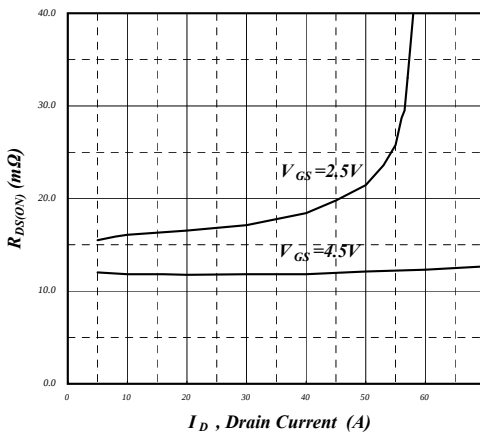


Fig 6. On-Resistance vs. Drain Current

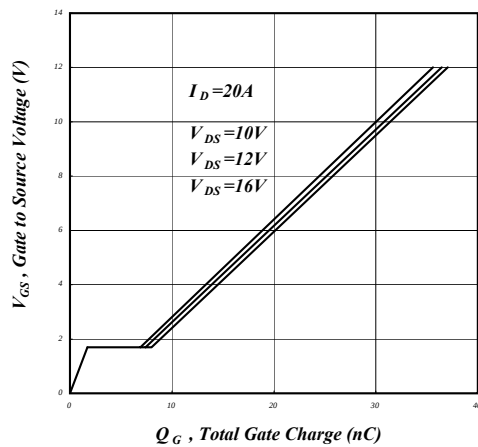


Fig 7. Gate Charge Characteristics

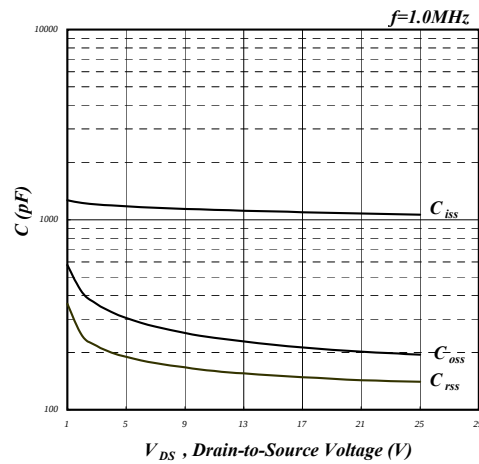


Fig 8. Typical Capacitance Characteristics

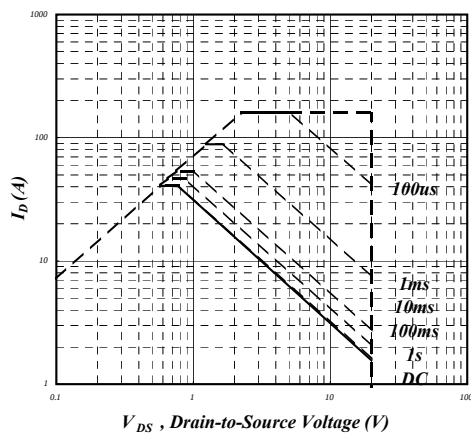


Fig 9. Maximum Safe Operating Area

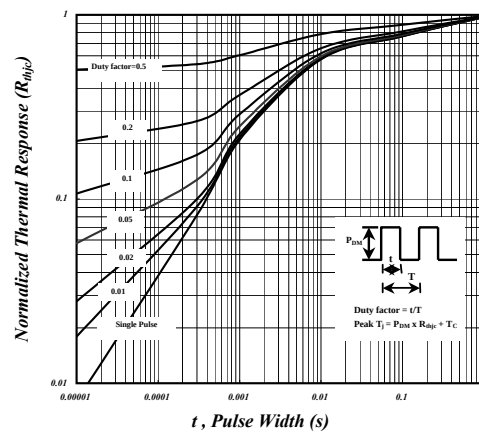


Fig 10. Effective Transient Thermal Impedance

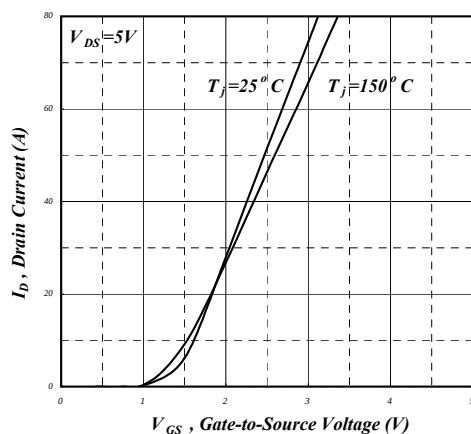


Fig 11. Transfer Characteristics

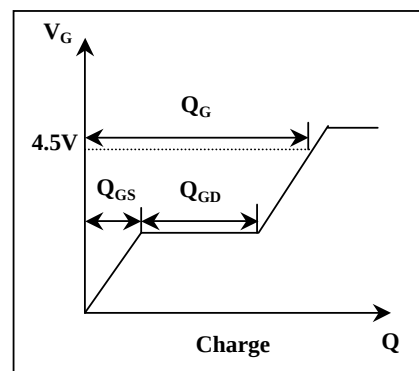


Fig 12. Gate Charge Waveform